74AHC1GU04-Q100

Inverter

Rev. 1 — 21 November 2012 | Product data sheet

1. General description

The 74AHC1GU04-Q100 is a high-speed Si-gate CMOS device. It provides an inverting single stage function.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC1GU04GW-Q100	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AHC1GU04GV-Q100	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753

4. Marking

Table 2. Marking codes

Type number	Marking
74AHC1GU04GW-Q100	AD
74AHC1GU04GV-Q100	AU4

5. Functional diagram

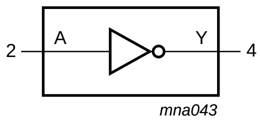


Fig 1. Logic symbol

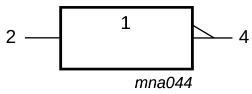


Fig 2. IEC logic symbol

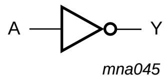


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

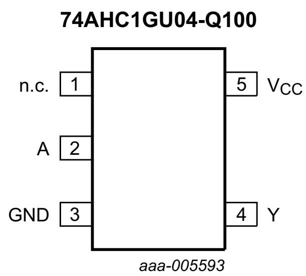


Fig 4. Pin configuration

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
n.c.	1	not connected
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V_{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Input	Output
A	**Y**
L	H
H	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < –0.5$ V		–20	-	mA
V_I	input voltage		[1]	–0.5	+7.0	V
I_{OK}	output clamping current	$V_O < –0.5$ V or $V_O > V_{CC} + 0.5$ V		-	±20	mA
I_O	output current	$–0.5\ V < V_O < V_{CC} + 0.5$ V		-	±25	mA
I_{CC}	supply current			-	75	mA
I_{GND}	ground current			–75	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[2]	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For both TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.3 V ± 0.3 V	-	-	100	ns/V
		V_{CC} = 5.0 V ± 0.5 V	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.7	-	-	1.7	-	1.7	-	V
		V_{CC} = 3.0 V	2.4	-	-	2.4	-	2.4	-	V
		V_{CC} = 5.5 V	4.4	-	-	4.4	-	4.4	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.3	-	0.3	-	0.3	V
		V_{CC} = 3.0 V	-	-	0.6	-	0.6	-	0.6	V
		V_{CC} = 5.5 V	-	-	1.1	-	1.1	-	1.1	V

Table 7. Static characteristics *...continued*

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		$I_O = –50\ \mu A$; $V_{CC} = 2.0\ V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = –50\ \mu A$; $V_{CC} = 3.0\ V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = –50\ \mu A$; $V_{CC} = 4.5\ V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = –4.0\ mA$; $V_{CC} = 3.0\ V$	2.58	-	-	2.48	-	2.40	-	V
		$I_O = –8.0\ mA$; $V_{CC} = 4.5\ V$	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		$I_O = 50\ \mu A$; $V_{CC} = 2.0\ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50\ \mu A$; $V_{CC} = 3.0\ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50\ \mu A$; $V_{CC} = 4.5\ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0\ mA$; $V_{CC} = 3.0\ V$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0\ mA$; $V_{CC} = 4.5\ V$	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	$V_I = 5.5\ V$ or GND; $V_{CC} = 0\ V$ to $5.5\ V$	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\ A$; $V_{CC} = 5.5\ V$	-	-	1.0	-	10	-	40	μA
C_I	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f = \leq 3.0$ ns. For test circuit see Figure 6.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	propagation delay	A to Y; see Figure 5 [1]								
		$V_{CC} = 3.0\ V$ to $3.6\ V$ [2]								
		$C_L = 15\ pF$	-	3.4	7.1	1.0	8.5	1.0	10.0	ns
		$C_L = 50\ pF$	-	4.9	10.6	1.0	12.0	1.0	13.5	ns
		$V_{CC} = 4.5\ V$ to $5.5\ V$ [3]								
		$C_L = 15\ pF$	-	2.6	5.5	1.0	6.0	1.0	7.0	ns
		$C_L = 50\ pF$	-	3.6	7.0	1.0	8.0	1.0	9.0	ns
C_{PD}	power dissipation capacitance	per buffer; $V_I = GND$ to V_{CC} [4]	-	14	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

[2] Typical values are measured at $V_{CC} = 3.3\ V$.

[3] Typical values are measured at $V_{CC} = 5.0\ V$.

[4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

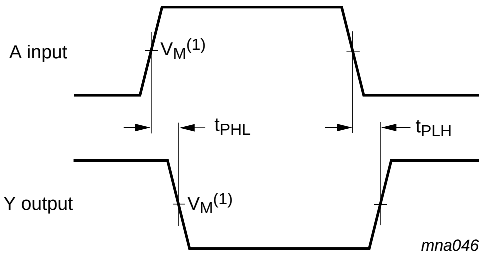
f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

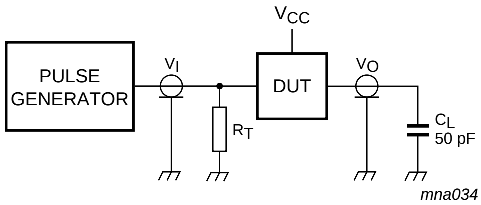
V_{CC} = supply voltage in Volts.

12. Waveforms



$V_M = 0.5 \times V_{CC}$; V_I = GND to V_{CC}.

Fig 5. The input (A) to output (Y) propagation delay times



Test data is given in Table 8.

Definitions for test circuit:

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 6. Load circuitry for switching times

13. Typical transfer characteristics

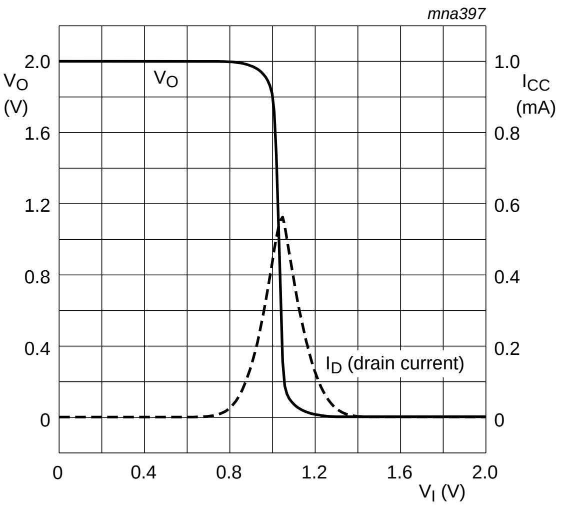


Fig 7. V_{CC} = 2.0 V; I_O = 0 A

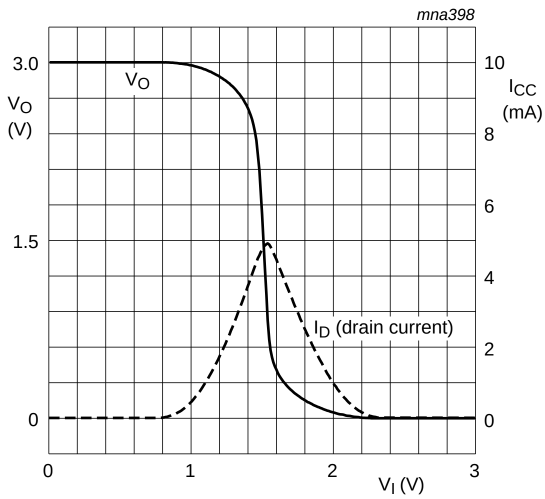


Fig 8. V_{CC} = 3.0 V; I_O = 0 A

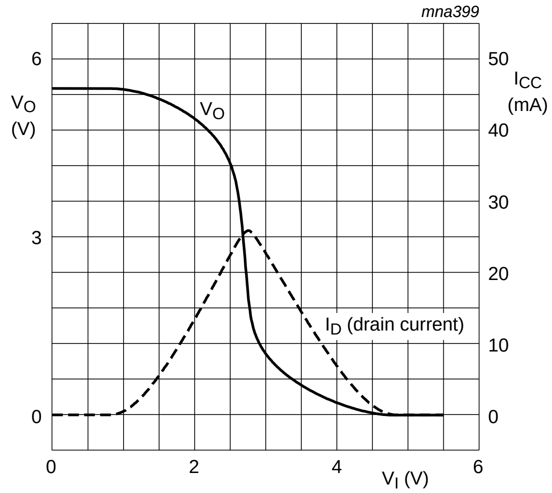


Fig 9. V_{CC} = 5.5 V; I_O = 0 A

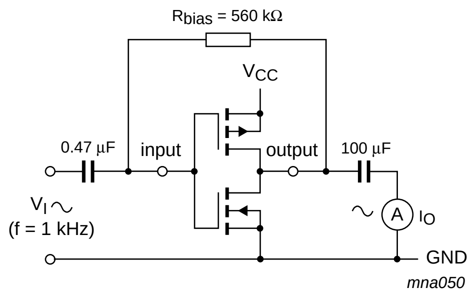


Fig 10. Test set-up for measuring forward transconductance $g_{fs} = \Delta I_O/\Delta V_I$ at V_O is constant

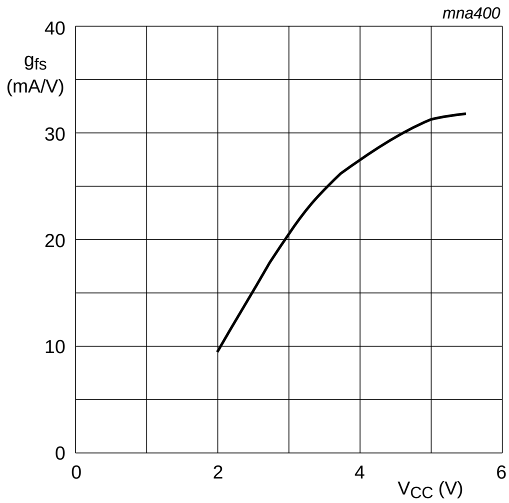


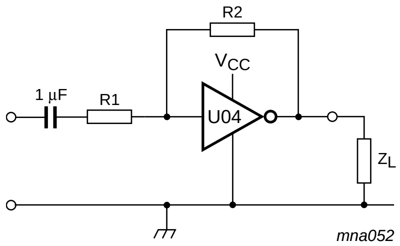
Fig 11. Typical forward transconductance g_{fs} as a function of the supply voltage at T_{amb} = 25 °C

14. Application information

Some applications are:

- Linear amplifier (see Figure 12)
- In crystal oscillator design (see Figure 13)

Remark: All values given are typical unless otherwise specified.



Maximum $V_{o(p-p)} = V_{CC} - 1.5$ V centered at $0.5 \times V_{CC}$.

$$G_v = -\frac{G_{ol}}{1 + \frac{R1}{R2}(1 + G_{ol})}$$

G_{ol} = open loop gain

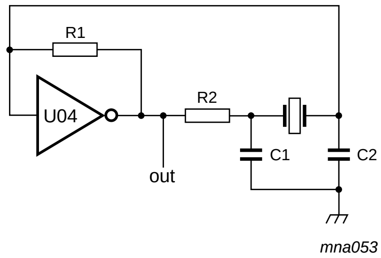
G_v = voltage gain

R1 ≥ 3 kΩ, R2 ≤ 1 MΩ

Z_L > 10 kΩ; G_{ol} = 20 (typical)

Typical unity gain bandwidth product is 5 MHz.

Fig 12. Used as a linear amplifier



C1 = 47 pF (typical)

C2 = 22 pF (typical)

R1 = 1 MΩ to 10 MΩ (typical)

R2 optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} (I_{CC} is typically 2 mA at V_{CC} = 3 V and f = 1 MHz).

Fig 13. Crystal oscillator configuration

Table 9. External components for resonator (f < 1 MHz)

All values given are typical and must be used as an initial set-up.

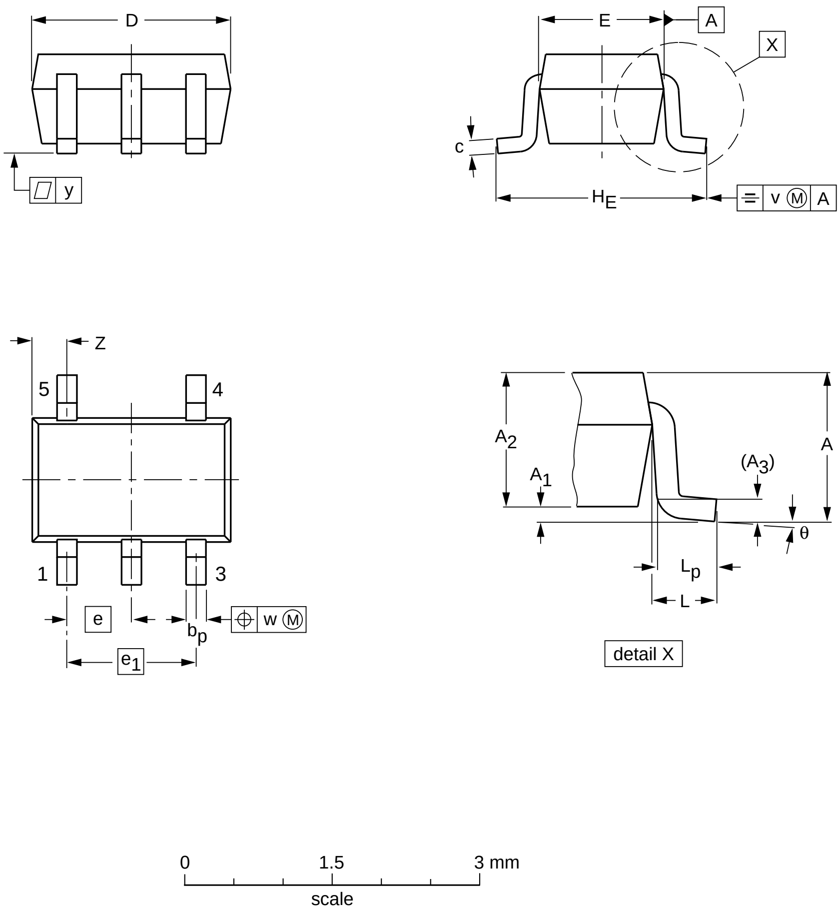
Frequency	R1	R2	C1	C2
10 kHz to 15.9 kHz	22 MΩ	220 kΩ	56 pF	20 pF
16 kHz to 24.9 kHz	22 MΩ	220 kΩ	56 pF	10 pF
25 kHz to 54.9 kHz	22 MΩ	100 kΩ	56 pF	10 pF
55 kHz to 129.9 kHz	22 MΩ	100 kΩ	47 pF	5 pF
130 kHz to 199.9 kHz	22 MΩ	47 kΩ	47 pF	5 pF
200 kHz to 349.9 kHz	22 MΩ	47 kΩ	47 pF	5 pF
350 kHz to 600 kHz	22 MΩ	47 kΩ	47 pF	5 pF

Table 10. Optimum value for R2

Frequency	R2	Optimum for
3 kHz	2.0 kΩ	minimum required I_{CC}
	8.0 kΩ	minimum influence due to change in V_{CC}
6 kHz	1.0 kΩ	minimum required I_{CC}
	4.7 kΩ	minimum influence by V_{CC}
10 kHz	0.5 kΩ	minimum required I_{CC}
	2.0 kΩ	minimum influence by V_{CC}
14 kHz	0.5 kΩ	minimum required I_{CC}
	1.0 kΩ	minimum influence by V_{CC}
>14 kHz	-	replace R2 by C3 with a typical value of 35 pF

15. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm **SOT353-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D(1)	E(1)	e	e_1	H_E	L	L_p	v	w	y	Z(1)	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

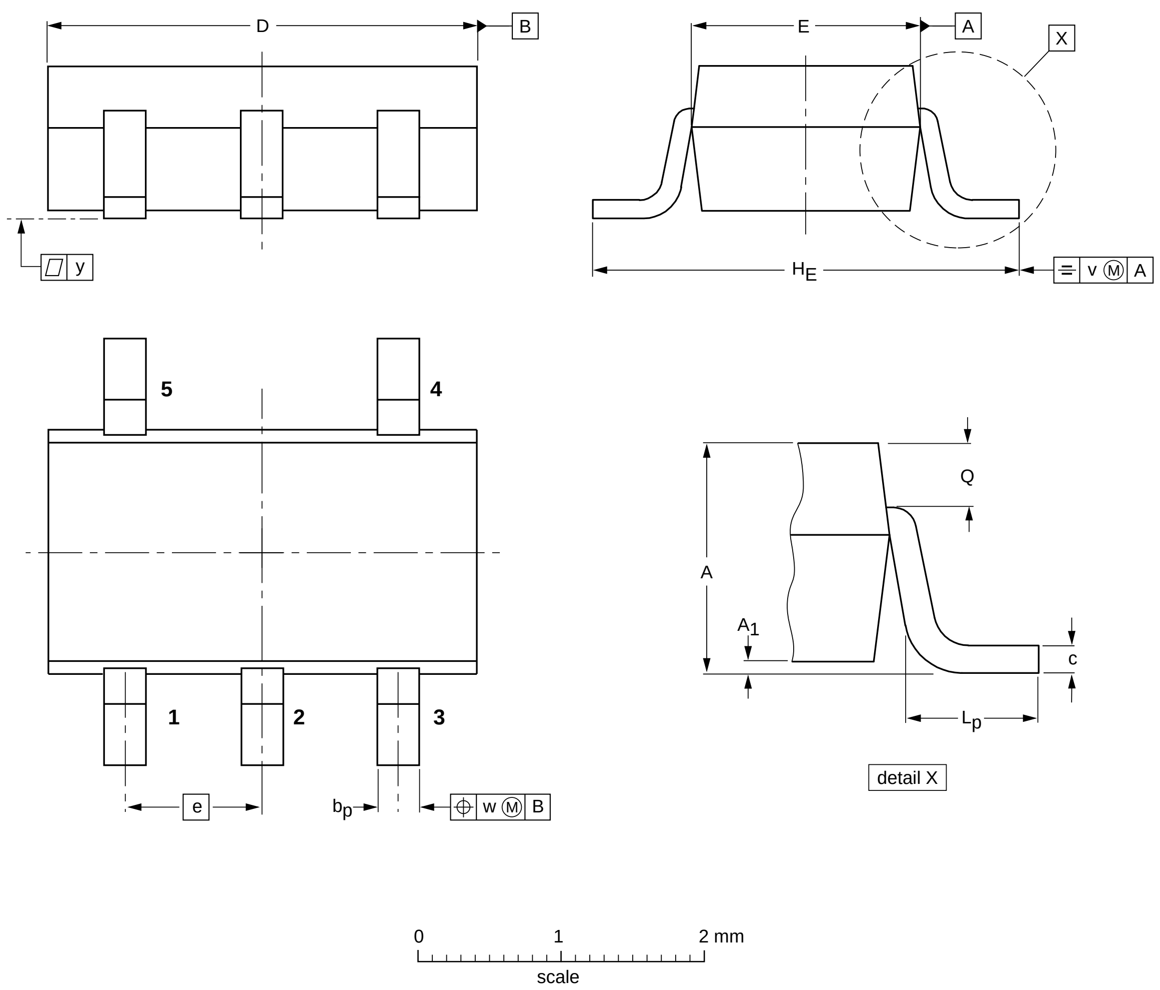
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			~~00-09-01~~ 03-02-19

Fig 14. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads **SOT753**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.100 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT753			SC-74A			~~02-04-16~~ 06-03-16

Fig 15. Package outline SOT753 (SC-74A)

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC1GU04_Q100 v.1	20121121	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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20. Contents

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Date of release: 21 November 2012

Document identifier: 74AHC1GU04_Q100